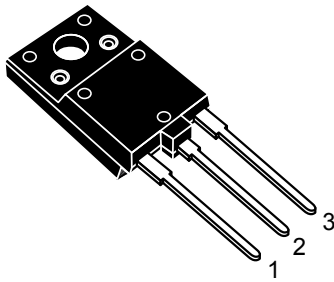
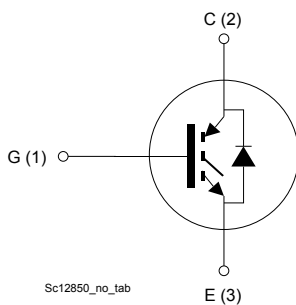


## Trench gate field-stop IGBT, V series 600 V, 30 A very high speed


**TO-3PF**


### Features

- Maximum junction temperature:  $T_J = 175\text{ °C}$
- Tail-less switching off
- $V_{CE(sat)} = 1.85\text{ V (typ.) @ } I_C = 30\text{ A}$
- Tight parameter distribution
- Safe paralleling
- Low thermal resistance
- Very fast soft recovery antiparallel diode

### Applications

- Photovoltaic inverters
- Uninterruptible power supply
- Welding
- Power factor correction
- Very high frequency converters

### Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the V series IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of very high frequency converters. Furthermore, the positive  $V_{CE(sat)}$  temperature coefficient and very tight parameter distribution result in safer paralleling operation.

#### Product status link

[STGFW30V60DF](#)

#### Product summary

<b>Order code</b>	STGFW30V60DF
<b>Marking</b>	G30V60DF
<b>Package</b>	TO-3PF
<b>Packing</b>	Tube

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage ( $V_{GE} = 0$ V)	600	V
$I_C$	Continuous collector current at $T_C = 25$ °C	60	A
	Continuous collector current at $T_C = 100$ °C	30	
$I_{CP}^{(1)}$	Pulsed collector current	120	A
$V_{GE}$	Gate-emitter voltage	$\pm 20$	V
$I_F$	Continuous forward current at $T_C = 25$ °C	60	A
	Continuous forward current at $T_C = 100$ °C	30	
$I_{FP}^{(1)}$	Pulsed forward current	120	
$P_{TOT}$	Total power dissipation at $T_C = 25$ °C	58	W
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t = 1$ s, $T_C = 25$ °C)	3.5	kV
$T_{STG}$	Storage temperature range	- 55 to 150	°C
$T_J$	Operating junction temperature range	- 55 to 175	

1. Pulse width limited by maximum junction temperature.

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance junction-case IGBT	2.6	°C/W
	Thermal resistance junction-case diode	3.4	
$R_{thJA}$	Thermal resistance junction-ambient	50	

## 2 Electrical characteristics

$T_J = 25\text{ °C}$  unless otherwise specified

**Table 3. Static characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}, I_C = 2\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 30\text{ A}$		1.85	2.3	V
		$V_{GE} = 15\text{ V}, I_C = 30\text{ A}, T_J = 125\text{ °C}$		2.15		
		$V_{GE} = 15\text{ V}, I_C = 30\text{ A}, T_J = 175\text{ °C}$		2.35		
$V_F$	Forward on-voltage	$I_F = 30\text{ A}$		2	2.6	V
		$I_F = 30\text{ A}, T_J = 125\text{ °C}$		1.7		
		$I_F = 30\text{ A}, T_J = 175\text{ °C}$		1.6		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$	5	6	7	V
$I_{CES}$	Collector cut-off current	$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$			25	$\mu\text{A}$
$I_{GES}$	Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			250	nA

**Table 4. Dynamic characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance	$V_{CE} = 25\text{ V}, f = 1\text{ MHz}, V_{GE} = 0\text{ V}$	-	3750	-	pF
$C_{oes}$	Output capacitance		-	120	-	pF
$C_{res}$	Reverse transfer capacitance		-	77	-	pF
$Q_g$	Total gate charge	$V_{CC} = 480\text{ V}, I_C = 30\text{ A}, V_{GE} = 15\text{ V}$ (see Figure 27. Gate charge test circuit)	-	163	-	nC
$Q_{ge}$	Gate-emitter charge		-	28	-	nC
$Q_{gc}$	Gate-collector charge		-	72	-	nC

**Table 5. IGBT switching characteristics (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$ , $I_C = 30\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ (see Figure 26. Test circuit for inductive load switching)	-	45	-	ns
$t_r$	Current rise time		-	16	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1500	-	A/ $\mu$ s
$t_{d(off)}$	Turn-off delay time		-	189	-	ns
$t_f$	Current fall time		-	19	-	ns
$E_{on}^{(1)}$	Turn-on switching energy		-	383	-	$\mu$ J
$E_{off}^{(2)}$	Turn-off switching energy		-	233	-	$\mu$ J
$E_{ts}$	Total switching energy		-	616	-	$\mu$ J
$t_{d(on)}$	Turn-on delay time		$V_{CE} = 400\text{ V}$ , $I_C = 30\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , $T_J = 175\text{ }^\circ\text{C}$ (see Figure 26. Test circuit for inductive load switching)	-	42	-
$t_r$	Current rise time	-		17	-	ns
$(di/dt)_{on}$	Turn-on current slope	-		1337	-	A/ $\mu$ s
$t_{d(off)}$	Turn-off-delay time	-		193	-	ns
$t_f$	Current fall time	-		32	-	ns
$E_{on}^{(1)}$	Turn-on switching energy	-		794	-	$\mu$ J
$E_{off}^{(2)}$	Turn-off switching energy	-		378	-	$\mu$ J
$E_{ts}$	Total switching energy	-		1172	-	$\mu$ J

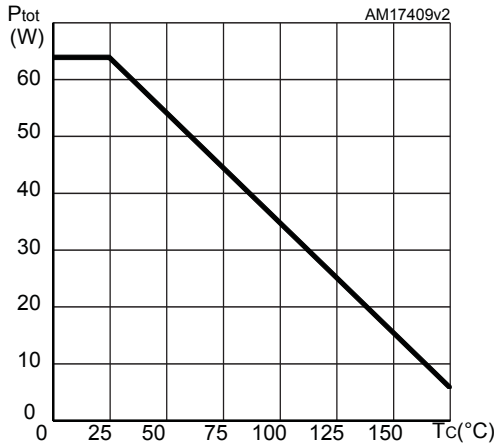
1. Energy losses include reverse recovery of the diode.
2. Turn-off losses include also the tail of the collector current.

**Table 6. Diode switching characteristics (inductive load)**

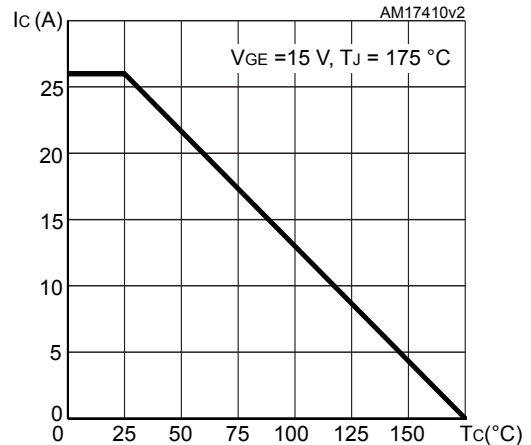
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{rr}$	Reverse recovery time	$I_F = 30\text{ A}$ , $V_R = 400\text{ V}$ , $V_{GE} = 15\text{ V}$ , $di/dt = 1000\text{ A}/\mu\text{s}$ (see Figure 26. Test circuit for inductive load switching)	-	53	-	ns
$Q_{rr}$	Reverse recovery charge		-	384	-	nC
$I_{rrm}$	Reverse recovery current		-	14.5	-	A
$dI_{rr}/dt$	Peak rate of fall of reverse recovery current during $t_b$		-	788	-	A/ $\mu$ s
$E_{rr}$	Reverse recovery energy		-	104	-	$\mu$ J
$t_{rr}$	Reverse recovery time		$I_F = 30\text{ A}$ , $V_R = 400\text{ V}$ , $V_{GE} = 15\text{ V}$ , $di/dt = 1000\text{ A}/\mu\text{s}$ , $T_J = 175\text{ }^\circ\text{C}$ (see Figure 26. Test circuit for inductive load switching)	-	104	-
$Q_{rr}$	Reverse recovery charge	-		1352	-	nC
$I_{rrm}$	Reverse recovery current	-		26	-	A
$dI_{rr}/dt$	Peak rate of fall of reverse recovery current during $t_b$	-		310	-	A/ $\mu$ s
$E_{rr}$	Reverse recovery energy	-		407	-	$\mu$ J

## 2.1 Electrical characteristics (curves)

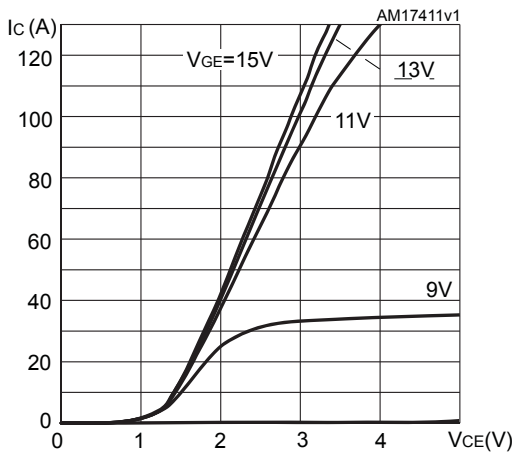
**Figure 1. Power dissipation vs case temperature**



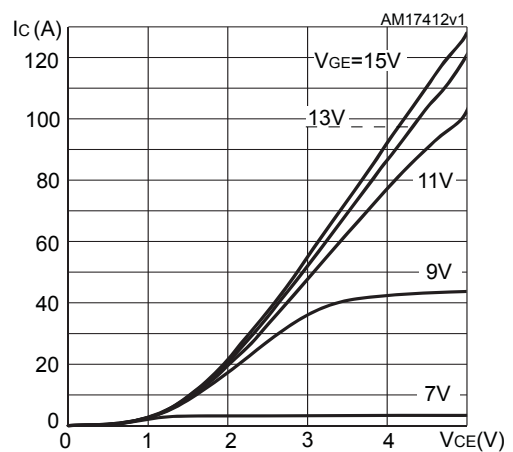
**Figure 2. Collector current vs case temperature**



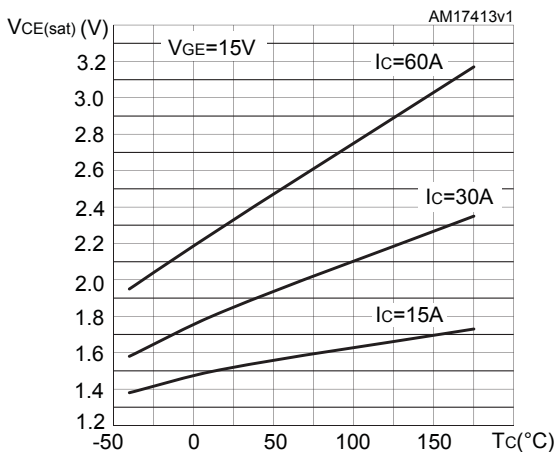
**Figure 3. Output characteristics ( $T_j = 25^\circ\text{C}$ )**



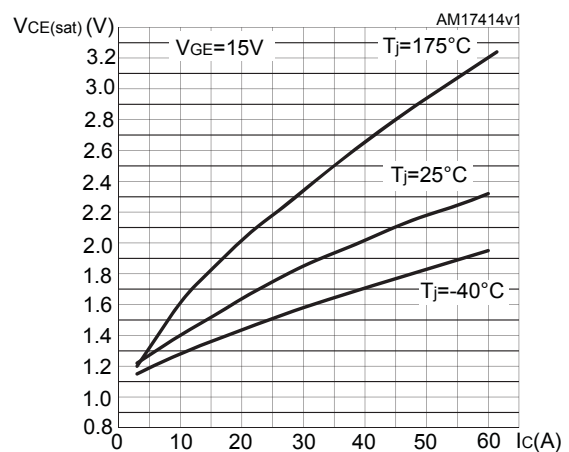
**Figure 4. Output characteristics ( $T_j = 175^\circ\text{C}$ )**



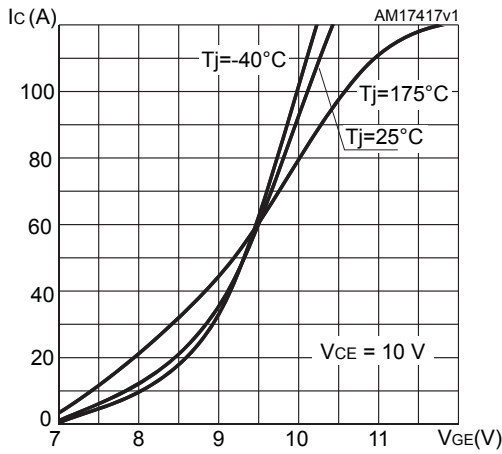
**Figure 5.  $V_{CE(sat)}$  vs junction temperature**



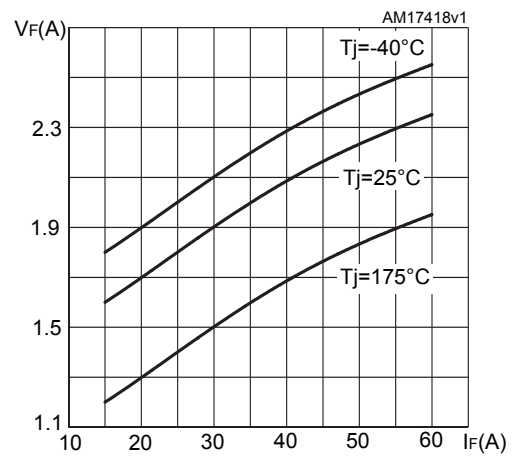
**Figure 6.  $V_{CE(sat)}$  vs collector current**



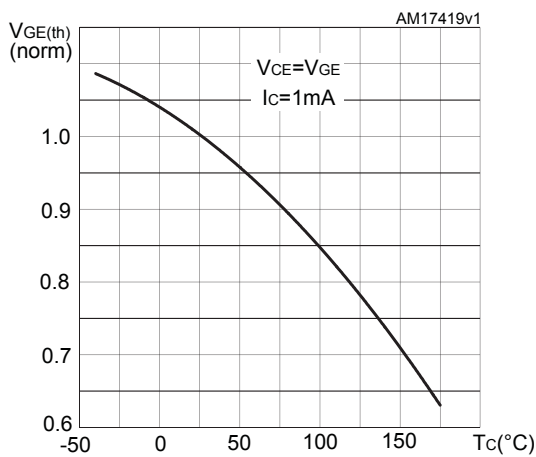
**Figure 7. Transfer characteristics**



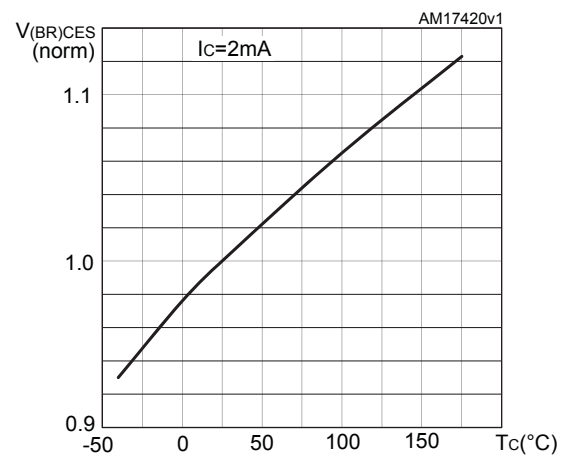
**Figure 8. Diode  $V_F$  vs forward current**



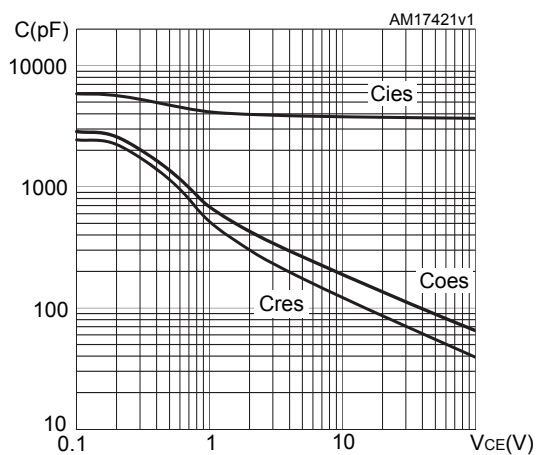
**Figure 9. Normalized  $V_{GE(th)}$  vs junction temperature**



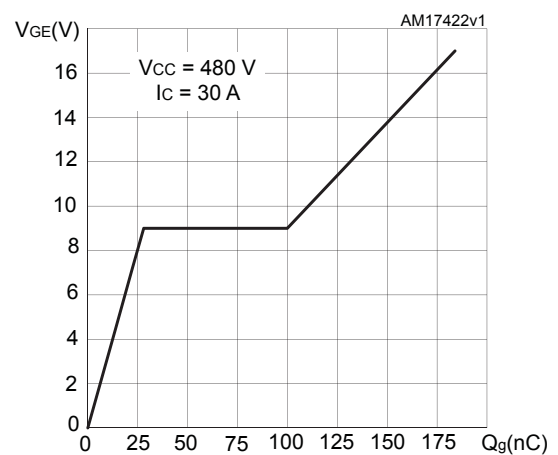
**Figure 10. Normalized  $V_{(BR)CES}$  vs junction temperature**



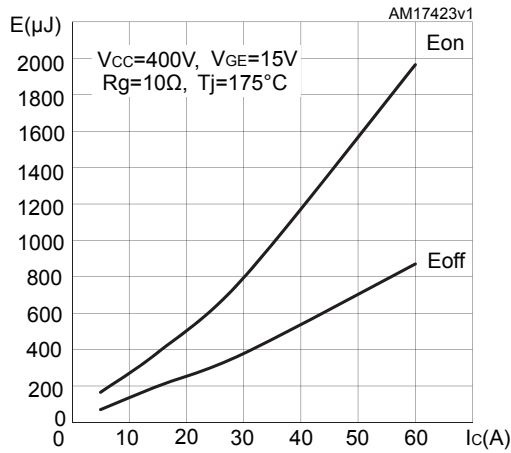
**Figure 11. Capacitance variations**



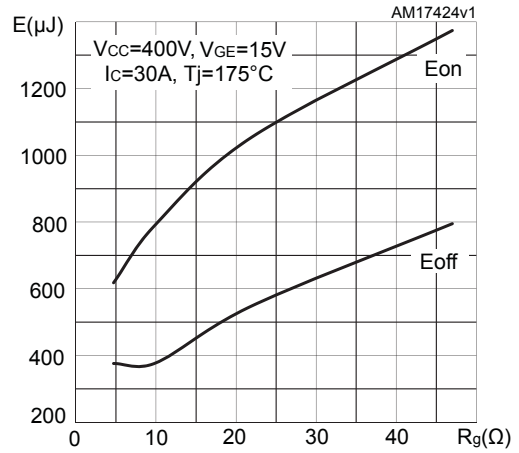
**Figure 12. Gate charge vs gate-emitter voltage**



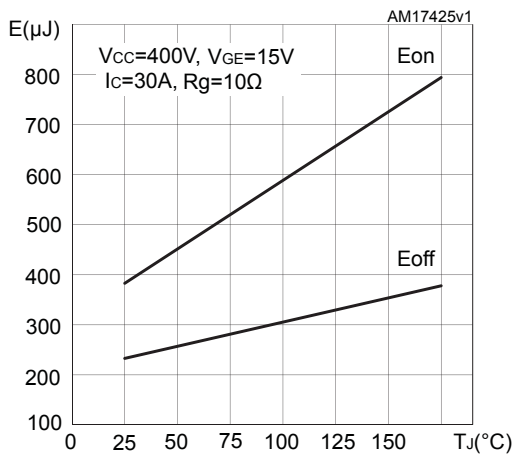
**Figure 13. Switching energy vs collector current**



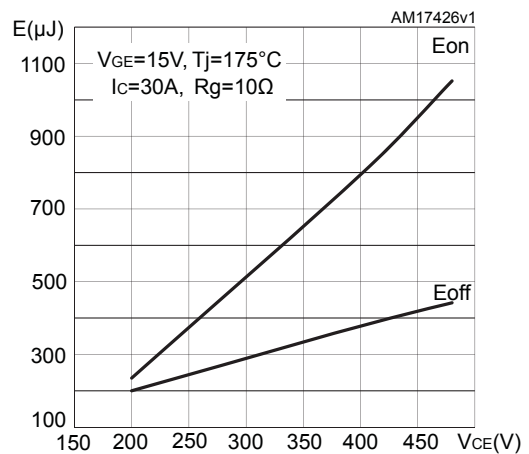
**Figure 14. Switching energy vs gate resistance**



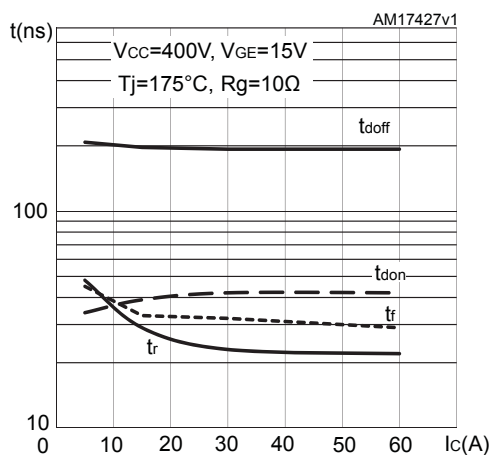
**Figure 15. Switching energy vs junction temperature**



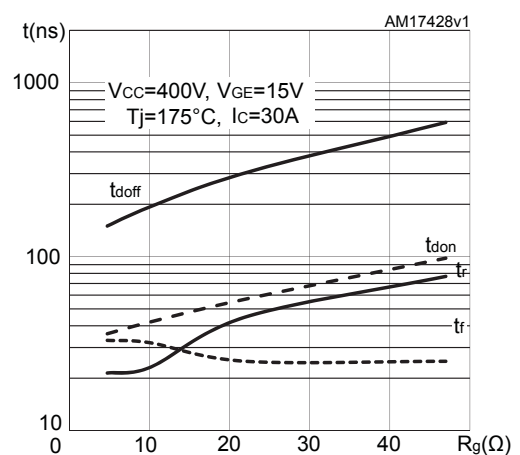
**Figure 16. Switching energy vs collector-emitter voltage**



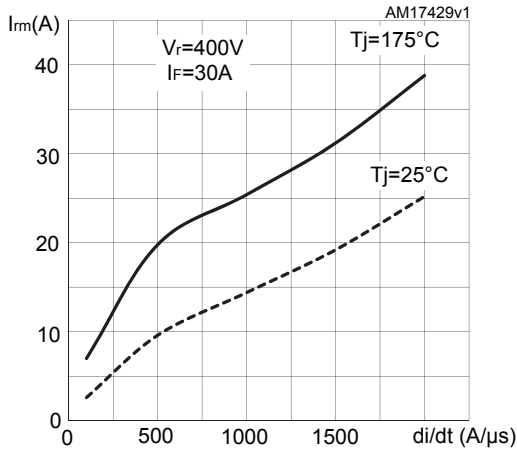
**Figure 17. Switching times vs collector current**



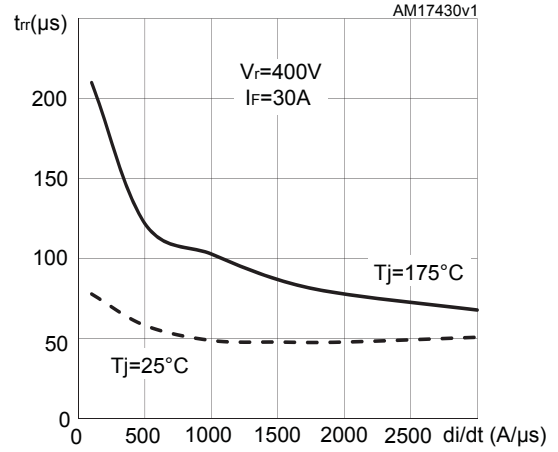
**Figure 18. Switching times vs gate resistance**



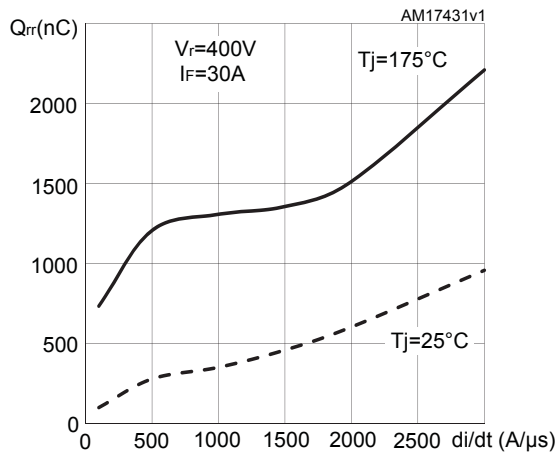
**Figure 19. Reverse recovery current vs diode current slope**



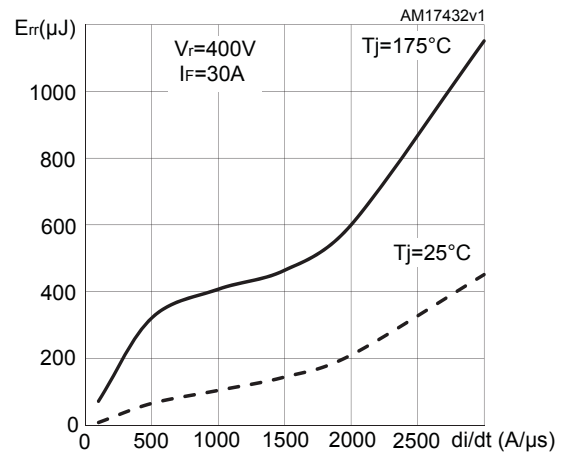
**Figure 20. Reverse recovery time vs diode current slope**



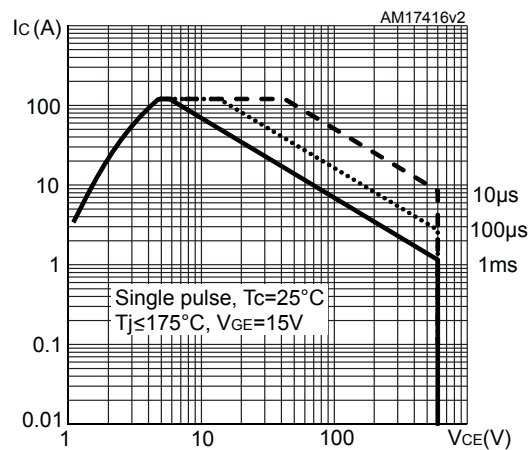
**Figure 21. Reverse recovery charge vs diode current slope**



**Figure 22. Reverse recovery energy vs diode current slope**

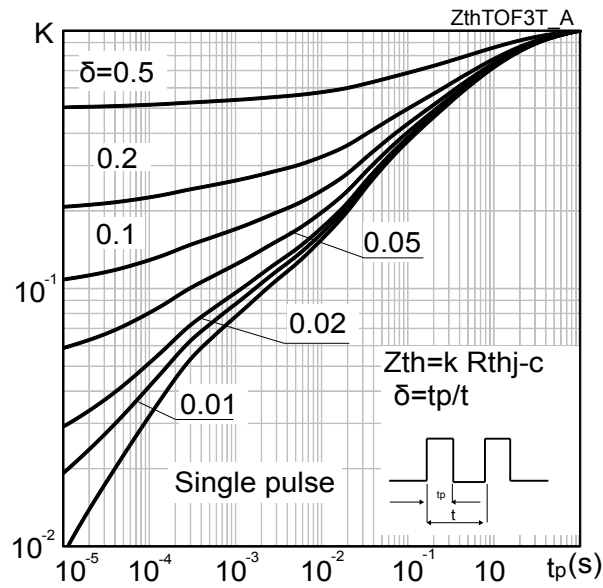


**Figure 23. Safe operating area**

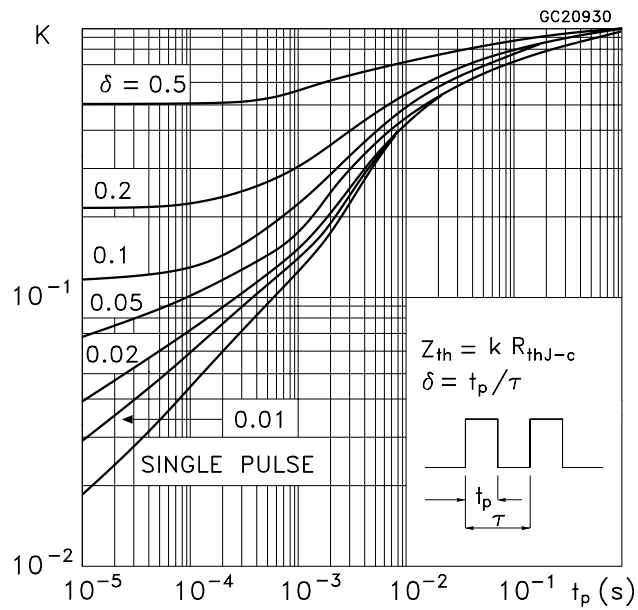




**Figure 24. Thermal impedance for IGBT**



**Figure 25. Thermal impedance for diode**



### 3 Test circuits

Figure 26. Test circuit for inductive load switching

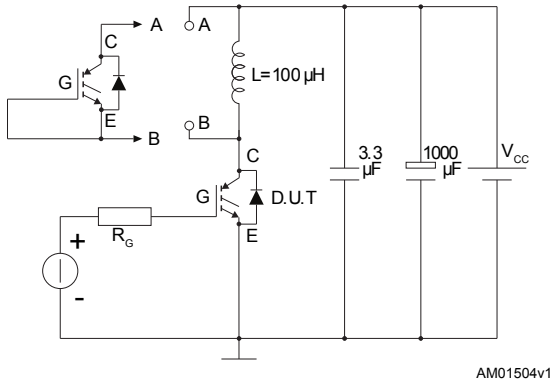


Figure 27. Gate charge test circuit

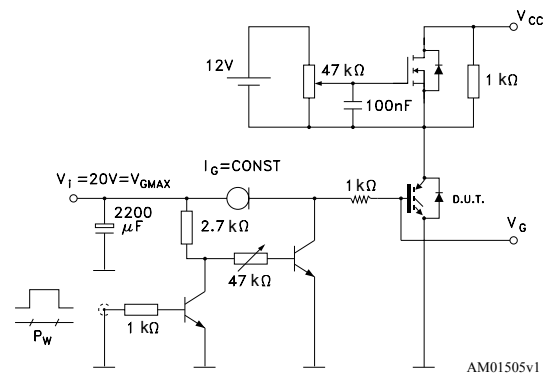


Figure 28. Switching waveform

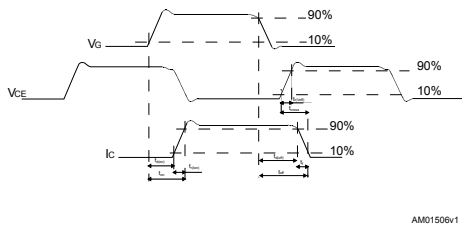
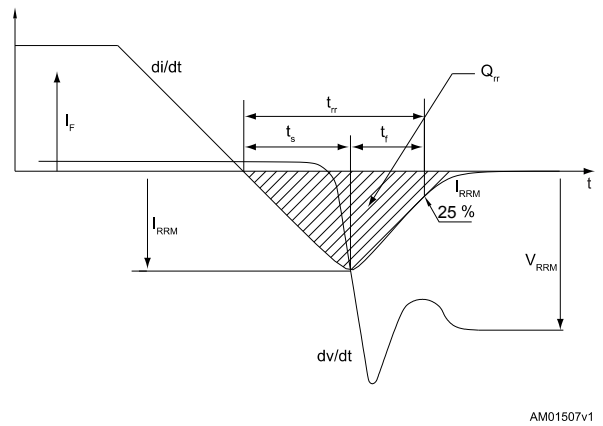


Figure 29. Diode reverse recovery waveform

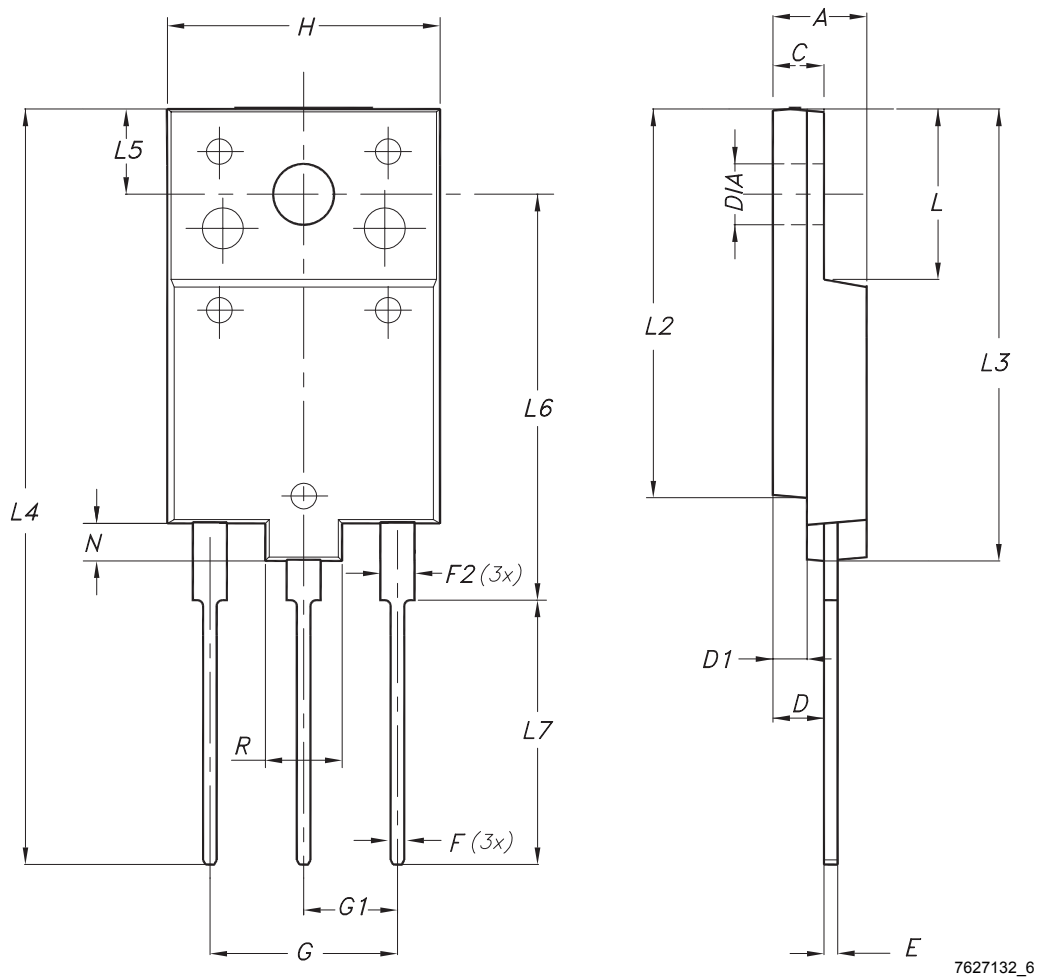


## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 4.1 TO-3PF package information

Figure 30. TO-3PF package outline



7627132\_6

**Table 7. TO-3PF mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	5.30		5.70
C	2.80		3.20
D	3.10		3.50
D1	1.80		2.20
E	0.80		1.10
F	0.65		0.95
F2	1.80		2.20
G	10.30		11.50
G1		5.45	
H	15.30		15.70
L	9.80	10.00	10.20
L2	22.80		23.20
L3	26.30		26.70
L4	43.20		44.40
L5	4.30		4.70
L6	24.30		24.70
L7	14.60		15.00
N	1.80		2.20
R	3.80		4.20
Dia	3.40		3.80

## Revision history

**Table 8. Document revision history**

Date	Revision	Changes
31-Mar-2014	1	Initial release.
14-Apr-2020	2	Updated <a href="#">Section Product status / summary</a> in cover page. Minor text changes.

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## Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>2</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>3</b>
<b>2.1</b>	<b>Electrical characteristics (curves)</b> .....	<b>5</b>
<b>3</b>	<b>Test circuits</b> .....	<b>10</b>
<b>4</b>	<b>Package information</b> .....	<b>11</b>
<b>4.1</b>	<b>TO-3PF package information</b> .....	<b>11</b>
	<b>Revision history</b> .....	<b>13</b>

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